

CMPT5551HC

**SURFACE MOUNT
HIGH CURRENT
NPN SILICON TRANSISTOR**



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5551HC type is a high current NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage and high current amplifier applications.

MARKING CODE: 1FHC

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 180
 V_{CEO} 160
 V_{EBO} 6.0
 I_C 1.0
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
V
V
A
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

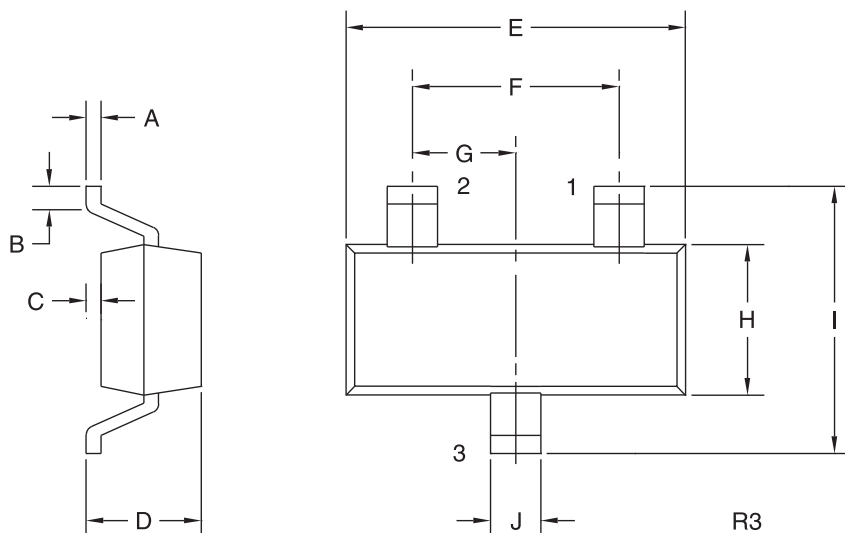
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=120\text{V}$			50	nA
I_{CBO}	$V_{CB}=120\text{V}, T_A=100^\circ\text{C}$			50	μA
I_{EBO}	$V_{EB}=4.0\text{V}$			50	nA
BV_{CBO}	$I_C=100\mu\text{A}$	180			V
BV_{CEO}	$I_C=1.0\text{mA}$	160			V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0			V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$			0.15	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$			0.20	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$			1.00	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$			1.00	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	80			
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	80		250	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	30			
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{A}$		10		
f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100			MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$			15	pF

R1 (1-February 2010)

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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: 1FHC

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (1-February 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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